

TOSHIBA Transistor Silicon PNP Triple Diffused Type

2SB1640

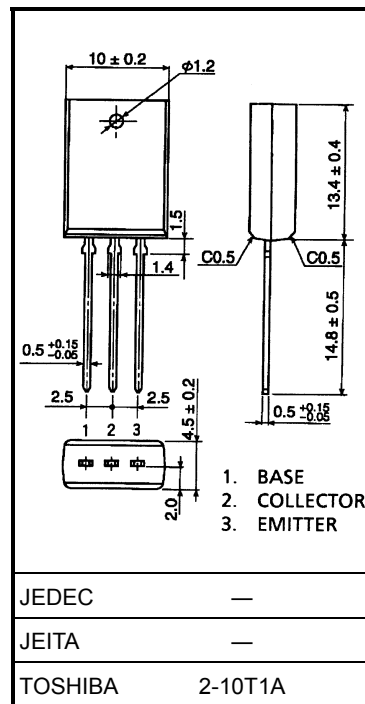
Audio Frequency Power Amplifier

Unit: mm

- Low saturation voltage: $V_{CE(sat)} = -1.5 \text{ V (max)}$
($I_C = -2 \text{ A}$, $I_B = -0.2 \text{ A}$)
- Collector metal (fin) is covered with mold region.
- Complementary to 2SD2525

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	-60	V
Collector-emitter voltage		V_{CEO}	-60	V
Emitter-base voltage		V_{EBO}	-7	V
Collector current	DC	I_C	-3	A
	Pulse	I_{CP}	-6	
Base current		I_B	-0.5	A
Collector power dissipation		P_C	1.8	W
Junction temperature		T_J	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

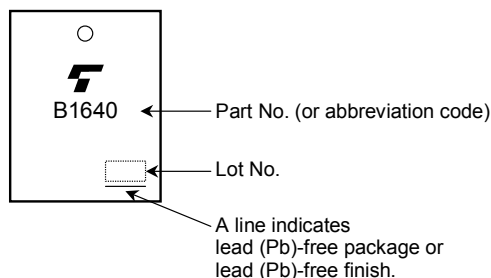


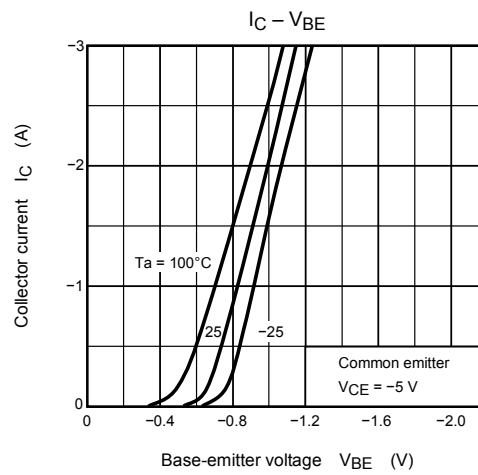
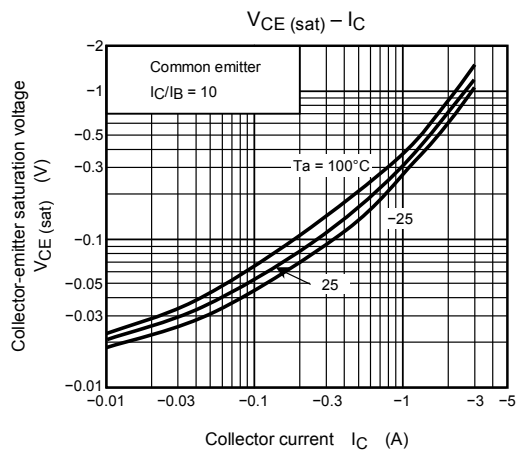
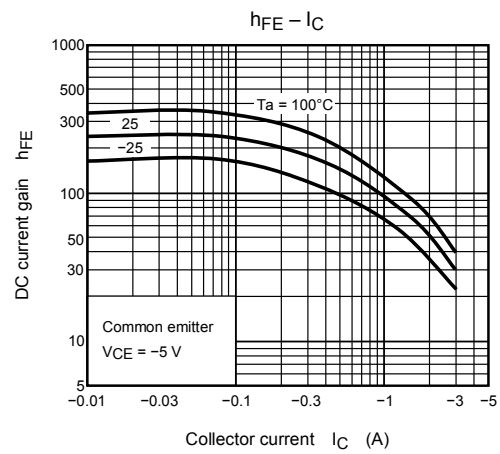
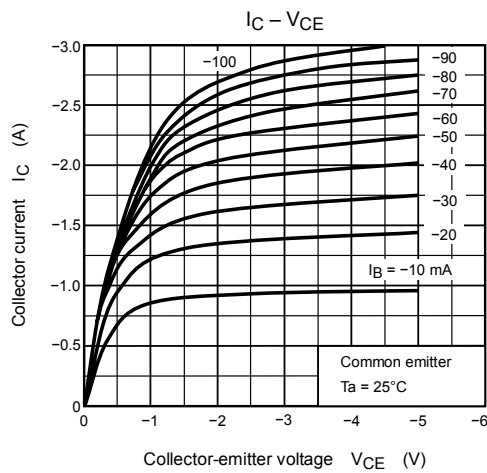
Weight: 1.5 g (typ.)

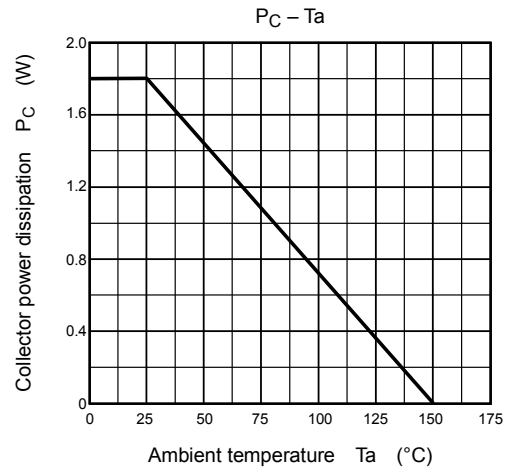
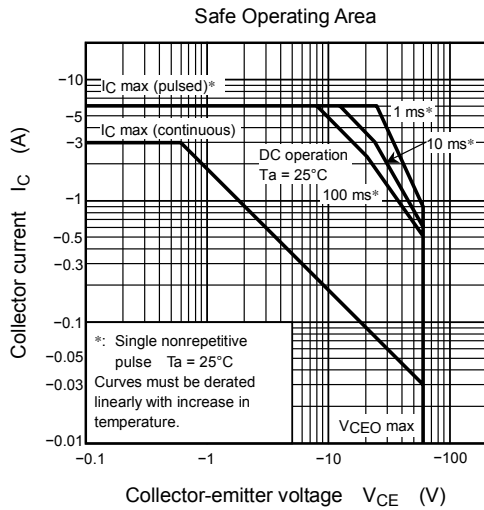
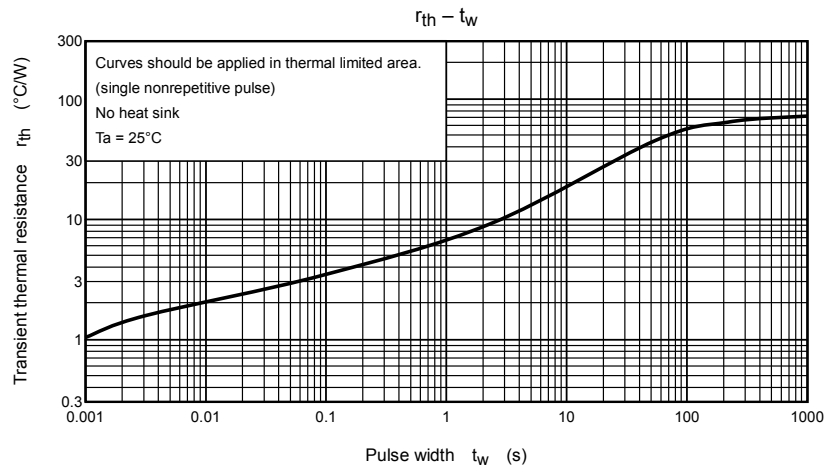
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -60 \text{ V}$, $I_E = 0$	—	—	-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -7 \text{ V}$, $I_C = 0$	—	—	-10	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -50 \text{ mA}$, $I_B = 0$	-60	—	—	V
DC current gain	$h_{FE(1)}$	$V_{CE} = -5 \text{ V}$, $I_C = -0.5 \text{ A}$	100	—	320	
	$h_{FE(2)}$	$V_{CE} = -5 \text{ V}$, $I_C = -2 \text{ A}$	15	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2 \text{ A}$, $I_B = -0.2 \text{ A}$	—	-0.1	-1.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5 \text{ V}$, $I_C = -0.5 \text{ A}$	—	-0.75	-1.0	V
Transition frequency	f_T	$V_{CE} = -5 \text{ V}$, $I_C = -0.5 \text{ A}$	—	9	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$	—	50	—	pF

Marking







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